查询2SB865供应商 捷多邦，专业PCB打样工厂，24小时加急出货

SANYO

No.828D

2SB865/2SD1153

PNP/ NPN Epitaxial Planar
Silicon Darlington Transistors

Drivers Applications

( ) : 2SB865

Uses

- Relay drivers, hammer drivers, lamp drivers, motor drivers

Features

- High DC current gain (4000 or more)
- Large current capacity and wide ASO
- Low saturation voltage

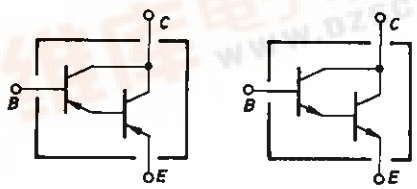
Absolute Maximum Ratings/T_a=25°C

			unit
Collector to Base Voltage	V_{CBO}	(−)80	V
Collector to Emitter Voltage	V_{CEO}	(−)50	V
Emitter to Base Voltage	V_{EBO}	(−)10	V
Collector Current	I_C	(−)1.5	A
Collector Current(Pulse)	I_{CP}	(−)3	A
Collector Dissipation	P_C	900	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	−55 to +150	°C

Electrical Characteristics/T_a=25°C

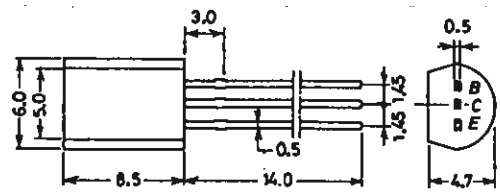
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	V_{CB}=(−)40V, I_E=0			(−)0.1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=(−)8V, I_C=0			(−)0.1	μA
DC current gain	$h_{FE}(1)$	V_{CE}=(−)2V, I_C=(−)500mA	4000			
	$h_{FE}(2)$	V_{CE}=(−)2V, I_C=(−)10mA	3000			
Gain-bandwidth product	f_T	V_{CE}=(−)10V, I_C=(−)50mA		120		MHz
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=(−)500mA, I_B=(−)0.5mA		(−)0.9	(−)1.5	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=(−)500mA, I_B=(−)0.5mA		(−)1.5	(−)2.0	V
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=(−)10μA, I_E=0	(−)80			V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=(−)1mA, R_{BE}=∞	(−)50			V
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=(−)10μA, I_C=0	(−)10			V

Electrical Connection



(2SB865) (2SD1153)

Package Dimensions 2006A
(unit: mm)



EIAJ: SC-51
SANYO: MP

B: Base
C: Collector
E: Emitter

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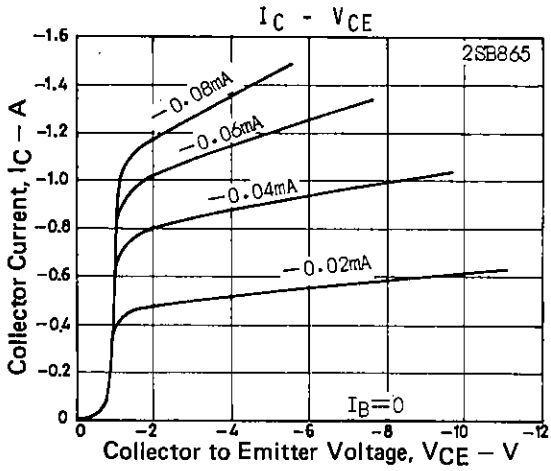
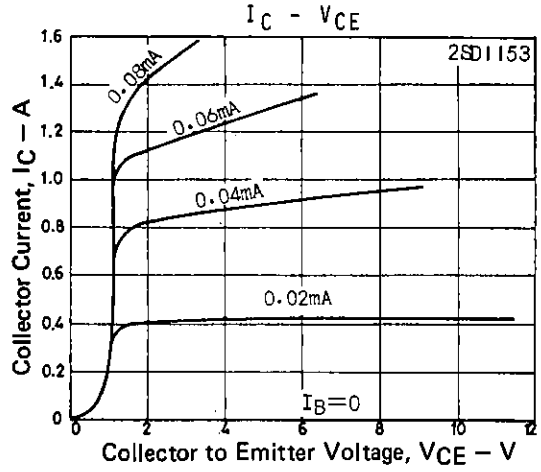
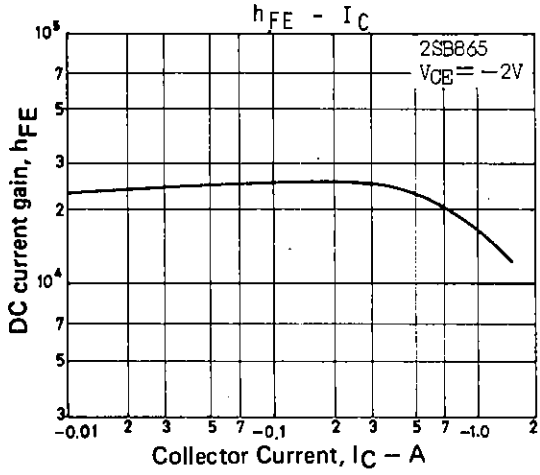
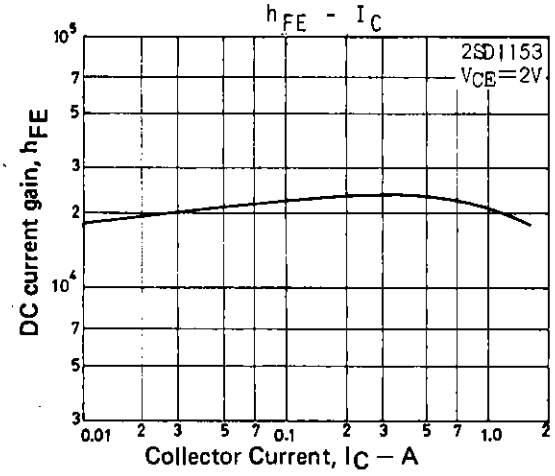
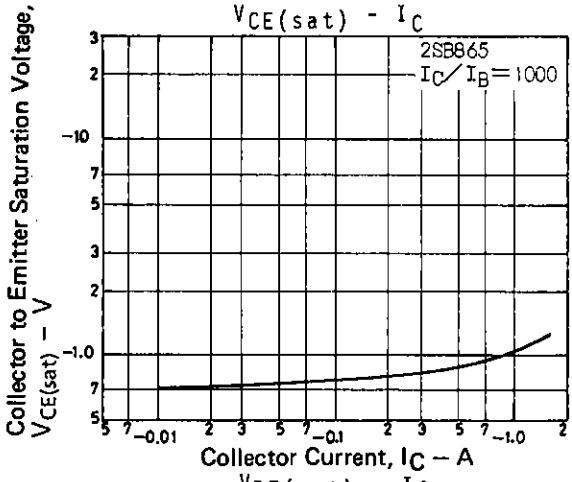
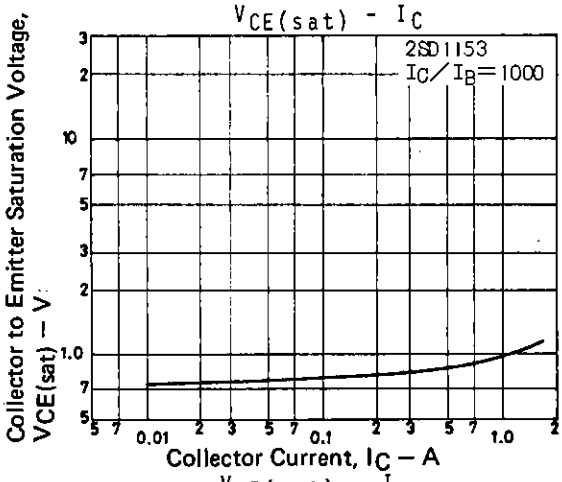

IC - VCE
2SB865
−0.08mA
−0.06mA
−0.04mA
−0.02mA
IB=0
Collector Current, IC − A
Collector to Emitter Voltage, VCE − V

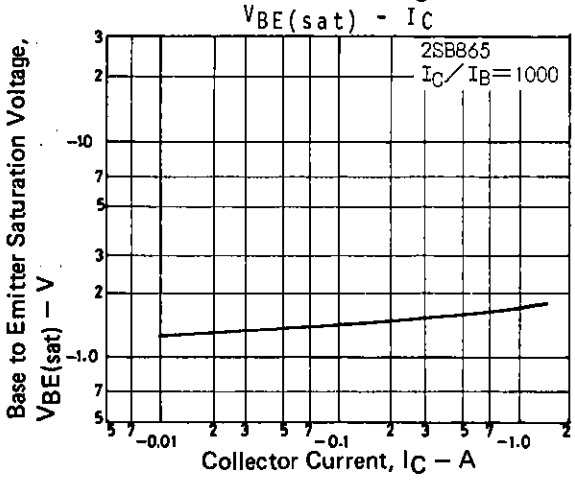

IC - VCE
2SD1153
0.08mA
0.06mA
0.04mA
0.02mA
IB=0
Collector Current, IC − A
Collector to Emitter Voltage, VCE − V

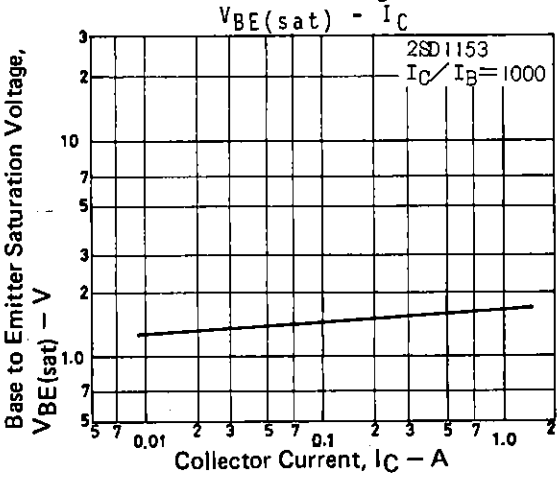

hFE - IC
2SB865
VCE=−2V
DC current gain, hFE
Collector Current, IC − A

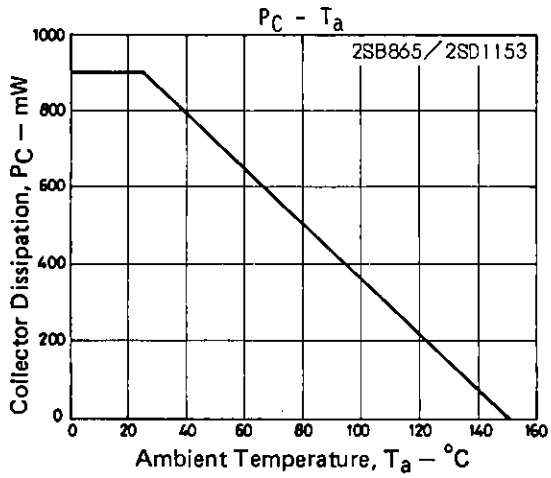

hFE - IC
2SD1153
VCE=2V
DC current gain, hFE
Collector Current, IC − A

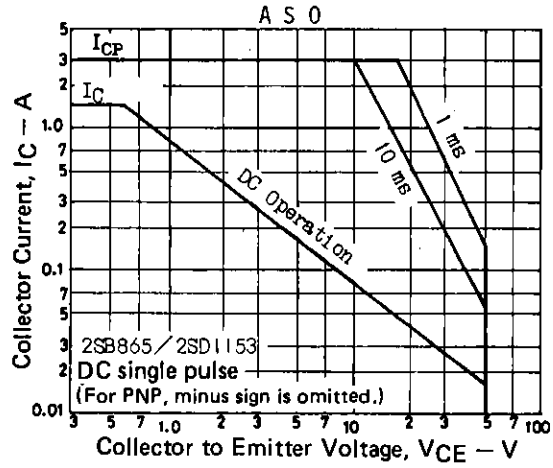

VCE(sat) - IC
2SB865
IC/IB=1000
Collector to Emitter Saturation Voltage, VCE(sat) − V
Collector Current, IC − A


VCE(sat) - IC
2SD1153
IC/IB=1000
Collector to Emitter Saturation Voltage, VCE(sat) − V
Collector Current, IC − A


VBE(sat) - IC
2SB865
IC/IB=1000
Base to Emitter Saturation Voltage, VBE(sat) − V
Collector Current, IC − A


VBE(sat) - IC
2SD1153
IC/IB=1000
Base to Emitter Saturation Voltage, VBE(sat) − V
Collector Current, IC − A





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